

Description

The AU0561D3 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The AU0561D3 complies with the IEC 61000-4-2 (ESD) with ±25 kV air and ±20 kV contact discharge. It is assembled into an ultra-small SOD-323 lead-free package. The small size and high ESD surge protection make AU0561D3 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Protects one data or power line
- Ultra low leakage: nA level
- Operating voltage: 5V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity testAir discharge: ±25kVContact discharge: ±20kV
 - IEC61000-4-5 (Lightning) 2A (8/20μs)
- RoHS Compliant

Mechanical Characteristics

- Package: SOD-323Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.Terminal Connections: See Diagram Below
- Marking Information: See Below

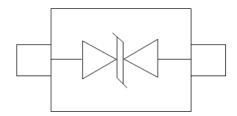
Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players
- Keypads, Side Keys, LCD Displays, USB2.0

Marking Information



Dimensions and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AU0561D3	3,000/Tape & Reel	7 inch



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

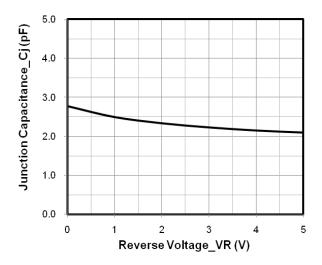
Parameter	Symbol	Value	Unit
ESD per IEC 61000-4-2 (Air)	\/F0D	±25	14) /
ESD per IEC 61000-4-2 (Contact)	VESD	±20	kV
Peak Pulse Power (8/20µs)	РРК	25	W
Peak Pulse Current	IPP	2	А
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

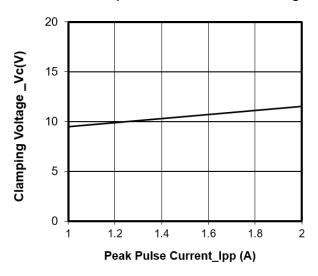
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6			V	IT = 1mA
Reverse Leakage Current	I _R			0.2	μA	VRWM = 5V
Clamping Voltage	Vc			10	V	IPP = 1A (8 x 20µs pulse)
Clamping Voltage	Vc			12.5	V	IPP = 2A (8 x 20µs pulse)
Junction Capacitance	Сл		3		pF	VR = 0V, f = 1MHz



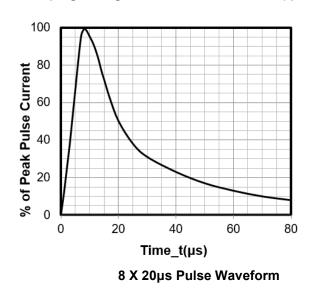
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

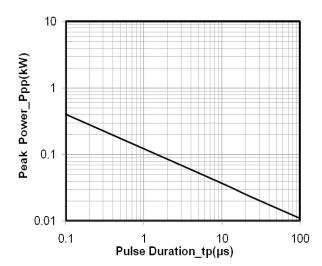


Junction Capacitance vs. Reverse Voltage

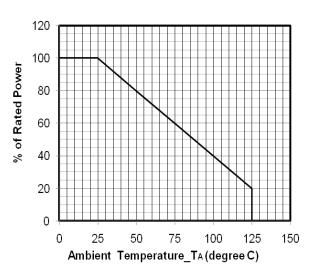


Clamping Voltage vs. Peak Pulse Current (tp = 8/20µs)

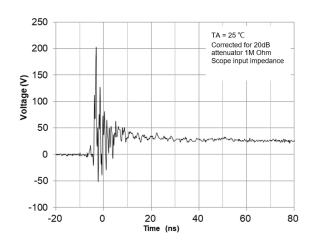




Peak Pulse Power vs. Pulse Time



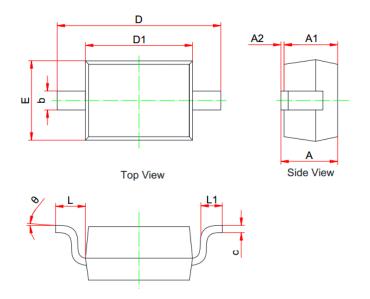
Power Derating Curve



ESD Clamping Voltage
-8 kV Contact per IEC61000-4-2

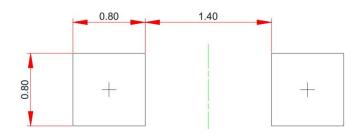


SOD-323 Package Outline Drawing



	MILLIMETERS					
	MIN	NOM	MAX			
Α	0.800		1.100			
A1	0.800		0.900			
A2	0.000	0.000				
b	0.250		0.400			
С	0.080		0.177			
D1	1.600	1.700	1.800			
D	2.300		2.800			
E	1.150		1.400			
L	0.475REF					
L1	0.100		0.500			
Θ	0°		8°			

Suggested Land Pattern



Unit: mm

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